The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1.-13. (Canceled)

14. (New) A luminescent device comprising:

a thin film transistor provided over an insulating surface;

a luminescent element electrically connected with said thin film transistor, comprising:

an organic compound layer containing an alkaline metal;

an anode; and

a cathode; and

at least one insulating layer provided between said thin film transistor and said luminescent element,

wherein said insulating layer is capable of adsorbing said alkaline metal.

15. (New) A device according to claim 14, wherein said at least one insulating layer comprises a silicon nitride film containing fluorine at a concentration of 1 x $10^{19}/cm^3$ or more.

16. (New) A device according to claim 14, wherein said at least one insulating layer comprises an organic resin film containing a particle comprising an antimony (Sb) compound, a tin (Sn) compound, or indium (In) compound.

17. (New) A device according to claim 14, wherein said at least one insulating layer comprises a laminated layer of a silicon nitride film containing fluorine at a

concentration of 1 x $10^{19}/cm^3$ or more and an organic resin film containing a particle comprising an antimony (Sb) compound, a tin (Sn) compound, or indium (In) compound.

18. (New) A device according to claim 14, wherein said insulating layer comprises a silicon oxynitride film or a silicon oxide film containing fluorine at a concentration of 1 x $10^{19}/cm^3$ or more.

19. (New) A luminescent device comprising:

a thin film transistor provided over an insulating surface;

a luminescent element electrically connected with said thin film transistor, comprising:

an organic compound layer;

an anode;

a buffer layer containing an alkaline metal; and

a cathode; and

at least one insulating layer provided between said thin film transistor and said luminescent element,

wherein said insulating layer is capable of adsorbing said alkaline metal.

20. (New) A device according to claim 19, wherein said at least one insulating layer comprises a silicon nitride film containing fluorine at a concentration of 1 x $10^{19}/cm^3$ or more.

21. (New) A device according to claim 19, wherein said at least one insulating layer comprises an organic resin film containing a particle comprising an antimony (Sb) compound, a tin (Sn) compound, or indium (In) compound.

22. (New) A device according to claim 19, wherein said at least one insulating layer comprises a laminated layer of a silicon nitride film containing fluorine at a concentration of 1 x $10^{19}/cm^3$ or more and an organic resin film containing a particle comprising an antimony (Sb) compound, a tin (Sn) compound, or indium (In) compound.

23. (New) A device according to claim 19, wherein said insulating layer comprises a silicon oxynitride film or a silicon oxide film containing fluorine at a concentration of 1 x $10^{19}/cm^3$ or more.

24. (New) A luminescent device comprising:

a thin film transistor provided over an insulating surface;

a luminescent element electrically connected with said thin film transistor, comprising:

an organic compound layer;

an anode; and

a cathode containing an alkaline-earth metal; and

at least one insulating layer provided between said thin film transistor and said luminescent element,

wherein said insulating layer is capable of adsorbing said alkaline-earth metal.

25. (New) A device according to claim 24, wherein said at least one insulating layer comprises a silicon nitride film containing fluorine at a concentration of 1 x $10^{19}/cm^3$ or more.

26. (New) A device according to claim 24, wherein said at least one insulating layer comprises an organic resin film containing a particle comprising an antimony (Sb) compound, a tin (Sn) compound, or indium (In) compound.

27. (New) A device according to claim 24, wherein said at least one insulating layer comprises a laminated layer of a silicon nitride film containing fluorine at a concentration of 1 x $10^{19}/cm^3$ or more and an organic resin film containing a particle comprising an antimony (Sb) compound, a tin (Sn) compound, or indium (In) compound.

28. (New) A device according to claim 24, wherein said insulating layer comprises a silicon oxynitride film or a silicon oxide film containing fluorine at a concentration of 1 x $10^{19}/cm^3$ or more.

29. (New) A luminescent device comprising:

a thin film transistor provided over an insulating surface;

a luminescent element electrically connected with said thin film transistor, comprising:

an organic compound layer containing an alkaline-earth metal;

an anode; and

a cathode; and

at least one insulating layer provided between said thin film transistor and said luminescent element,

wherein said insulating layer is capable of adsorbing said alkaline-earth metal.

30. (New) A device according to claim 29, wherein said at least one insulating layer comprises a silicon nitride film containing fluorine at a concentration of 1 x $10^{19}/cm^3$ or more.

31. (New) A device according to claim 29, wherein said at least one insulating layer comprises an organic resin film containing a particle comprising an antimony (Sb) compound, a tin (Sn) compound, or indium (In) compound.

32. (New) A device according to claim 29, wherein said at least one insulating layer comprises a laminated layer of a silicon nitride film containing fluorine at a concentration of 1 x $10^{19}/cm^3$ or more and an organic resin film containing a particle comprising an antimony (Sb) compound, a tin (Sn) compound, or indium (In) compound.

33. (New) A device according to claim 29, wherein said insulating layer comprises a silicon oxynitride film or a silicon oxide film containing fluorine at a concentration of 1 x $10^{19}/cm^3$ or more.

34. (New) A luminescent device comprising:

a thin film transistor provided over an insulating surface of a substrate;

a luminescent element electrically connected with said thin film transistor, comprising:

an organic compound layer;

an anode;

a buffer layer containing an alkaline-earth metal; and

a cathode; and

at least one insulating layer provided between said thin film transistor and said luminescent element

wherein said insulating layer is capable of adsorbing said alkaline-earth metal.

35. (New) A device according to claim 34, wherein said at least one insulating layer comprises a silicon nitride film containing fluorine at a concentration of 1 x $10^{19}/cm^3$ or more.

36. (New) A device according to claim 34, wherein said at least one insulating layer comprises an organic resin film containing a particle comprising an antimony (Sb) compound, a tin (Sn) compound, or indium (In) compound.

37. (New) A device according to claim 34, wherein said at least one insulating layer comprises a laminated layer of a silicon nitride film containing fluorine at a concentration of 1 x $10^{19}/cm^3$ or more and an organic resin film containing a particle comprising an antimony (Sb) compound, a tin (Sn) compound, or indium (In) compound.

38. (New) A device according to claim 34, wherein said insulating layer comprises a silicon oxynitride film or a silicon oxide film containing fluorine at a concentration of 1 x $10^{19}/cm^3$ or more.